International Rectifier

AUTOMOTIVE GRADE

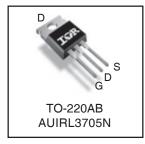
AUIRL3705N

Features HEXFET® Power MOSFET

- Advanced Planar Technology
- Logic-Level Gate Drive
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *

G S

V _{(BR)DSS}	55V
R _{DS(on)} max.	0.01Ω
I _D	89A⑤



G	D	S
Gate	Drain	Source

Description

Specifically designed for Automotive applications, this Cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low onresistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	89⑤	
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	63	А
рм	Pulsed Drain Current ①	310	
P _D @T _C = 25°C	Power Dissipation	170	
	Linear Derating Factor	101	W/°C
V _{GS}	Gate-to-Source Voltage	±16	V
= _{AS}	Single Pulse Avalanche Energy ②	340	mJ
Avalanche Current ①		46	А
= _{AR}	Repetitive Avalanche Energy ①	17	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T _J	Operating Junction and	-55 to + 175	
T _{STG}	Storage Temperature Range		°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Junction-to-Case		0.90	
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50		
$R_{\theta JA}$	Junction-to-Ambient		62	°C/W

Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	55			V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient		0.056		V/°C	Reference to 25°C, I _D = 1mA
				0.010		V _{GS} = 10V, I _D = 46A ④
R _{DS(on)}	Static Drain-to-Source On-Resistance			0.012	Ω	V _{GS} = 5.0V, I _D = 46A ④
				0.018		V _{GS} = 4.0V, I _D = 39A ⁽⁴⁾
V _{GS(th)}	Gate Threshold Voltage	1.0		2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
gfs	Forward Transconductance	50			S	V _{DS} = 25V, I _D = 46A ^⑤
I _{DSS}	Drain-to-Source Leakage Current			25	μΑ	$V_{DS} = 55V, V_{GS} = 0V$
				250		$V_{DS} = 44V, V_{GS} = 0V, T_{J} = 150^{\circ}C$
I _{GSS}	Gate-to-Source Forward Leakage			100	nA	V _{GS} = 16V
	Gate-to-Source Reverse Leakage			-100	1	V _{GS} = -16V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

- y		· • (· opco.	
Q_g	Total Gate Charge			98		$I_D = 46A$
Q _{gs}	Gate-to-Source Charge			19	nC	$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge			49		$V_{GS} = 5.0V$, See Fig 6 and 13 \oplus
t _{d(on)}	Turn-On Delay Time		12			V _{DD} = 28V
t _r	Rise Time		140			$I_D = 46A$
t _{d(off)}	Turn-Off Delay Time		37		ns	$R_G = 1.8\Omega$, $V_{GS} = 5.0V$
t _f	Fall Time		78			$R_D = 0.59\Omega$, See Fig.10 ④
L _D	Internal Drain Inductance		4.5		nH	Between lead, 6mm (0.25in.)
L _S	Internal Source Inductance		7.5			from package and center of die contact
C _{iss}	Input Capacitance		3600			V _{GS} = 0V
C _{oss}	Output Capacitance	_	870		рF	$V_{DS} = 25V$
C _{rss}	Reverse Transfer Capacitance	T —	320		1	f = 1.0MHz, See Fig.5

Diode Characteristics

	Parameter	Min.	Тур.	Max.	Units	Conditions
I _S	Continuous Source Current			89©		MOSFET symbol
	(Body Diode)			099	Α	showing the
I _{SM}	Pulsed Source Current			310] ^	integral reverse
	(Body Diode) ①			310		p-n junction diode.
V_{SD}	Diode Forward Voltage			1.3	V	$T_J = 25^{\circ}C, I_S = 46A, V_{GS} = 0V $ ④
t _{rr}	Reverse Recovery Time		94	140	ns	$T_J = 25$ °C, $I_F = 46A$
Q _{rr}	Reverse Recovery Charge		290	440	nC	di/dt = 100A/µs
t _{on}	Forward Turn-On Time	Intrinsio	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)			

Notes

- \odot Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- $^{\circ}$ V_{DD} = 25V, starting T_J = 25°C, L = 320 μ H, R_G = 25 Ω , I_{AS} = 46A. (See Figure 12)
- $\ \, \text{ } 3 \text{ } \text{ } I_{SD} \leq 46\text{A}, \text{ } \text{di/dt} \leq 250\text{A/}\mu\text{s}, \text{ } V_{DD} \leq V_{(BR)DSS}, \text{ } T_{J} \leq 175^{\circ}\text{C}$
- 4 Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.
- ⑤ Calculated continuous current based on maximum allowable junction temperature. for recommended current-handling of the package refer to Design tip # 93-4



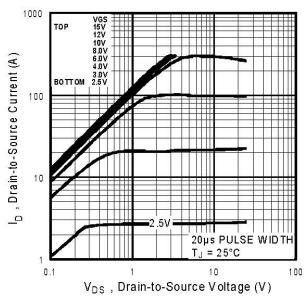
Qualification Information[†]

		Automotive (per AEC-Q101) ††				
		qualification.	This part number(s) passed Automotive R's Industrial and Consumer qualification by extension of the higher Automotive level.			
Moisture Sensitivity Level		3L-TO-220	N/A			
	Machine Model	Class M4(+/- 800V) ^{†††} (per AEC-Q101-002)				
ESD	Human Body Model	Class H1C(+/- 2000V) ^{†††} (per AEC-Q101-001)				
	Charged Device Model	Class C5(+/- 2000V) ^{†††} (per AEC-Q101-005)				
RoHS Complia	nt	Yes				

[†] Qualification standards can be found at International Rectifier's web site: http://www.irf.com/

^{††} Exceptions to AEC-Q101 requirements are noted in the qualification report.

^{†††} Highest passing voltage



 V_{DS} , Drain-to-Source Voltage (V) $\label{eq:DS} \textbf{Fig 1.} \ \, \text{Typical Output Characteristics}$

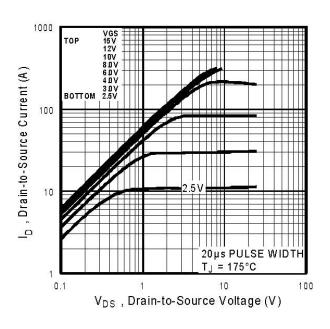


Fig 2. Typical Output Characteristics

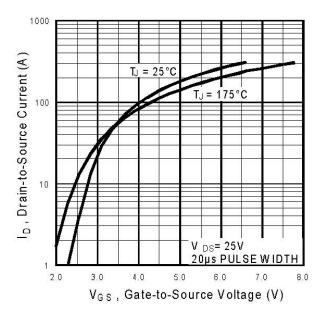


Fig 3. Typical Transfer Characteristics

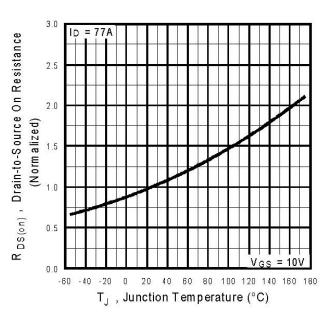


Fig 4. Normalized On-Resistance Vs. Temperature

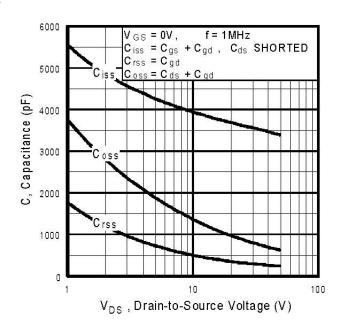


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

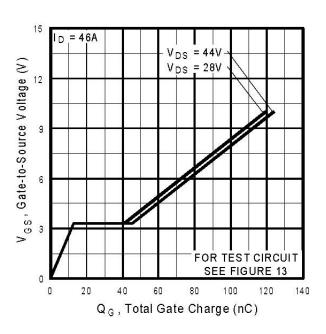


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

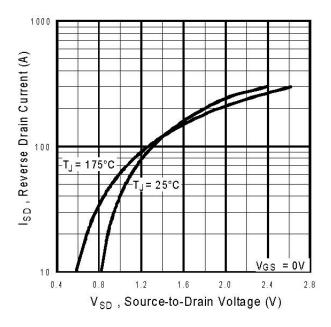


Fig 7. Typical Source-Drain Diode Forward Voltage

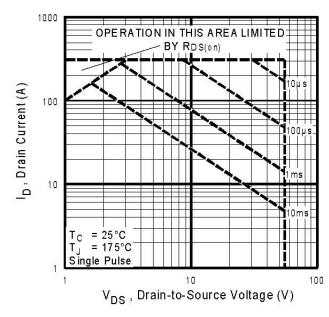


Fig 8. Maximum Safe Operating Area

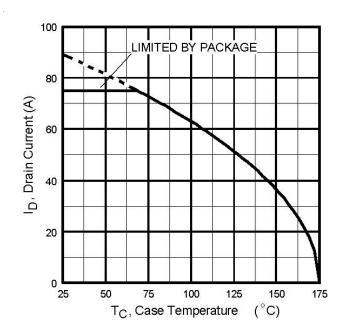


Fig 9. Maximum Drain Current Vs. Case Temperature

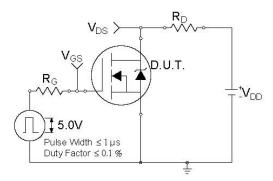


Fig 10a. Switching Time Test Circuit

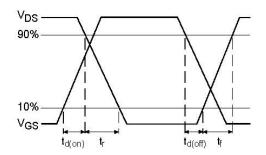


Fig 10b. Switching Time Waveforms

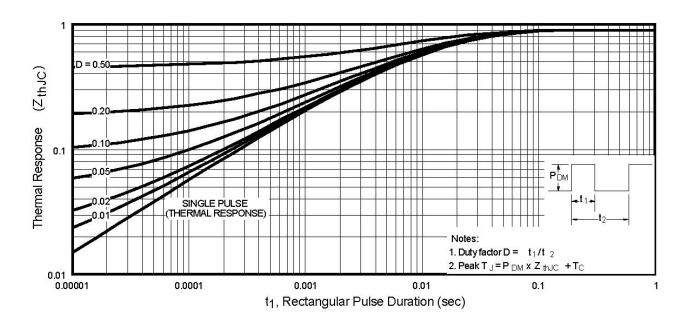


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

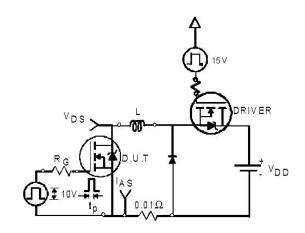


Fig 12a. Unclamped Inductive Test Circuit

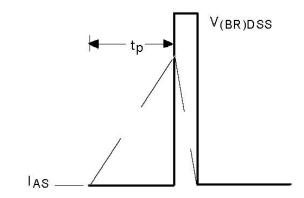


Fig 12b. Unclamped Inductive Waveforms

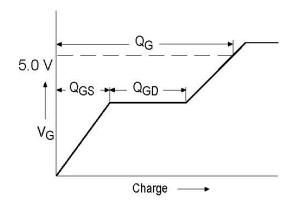


Fig 13a. Basic Gate Charge Waveform

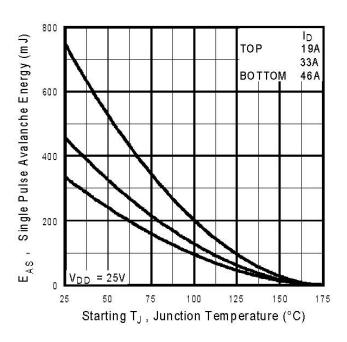


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

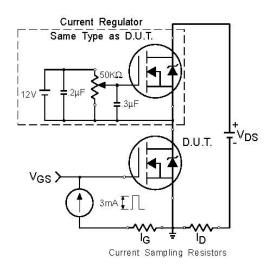
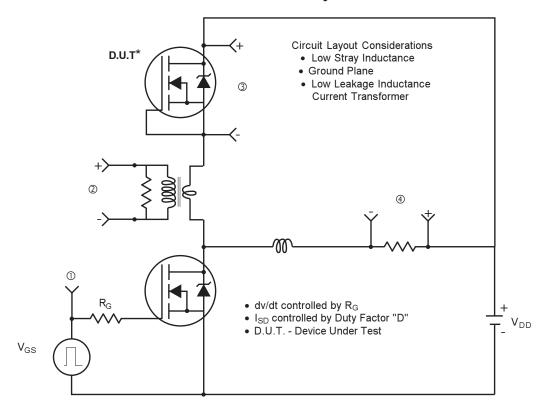
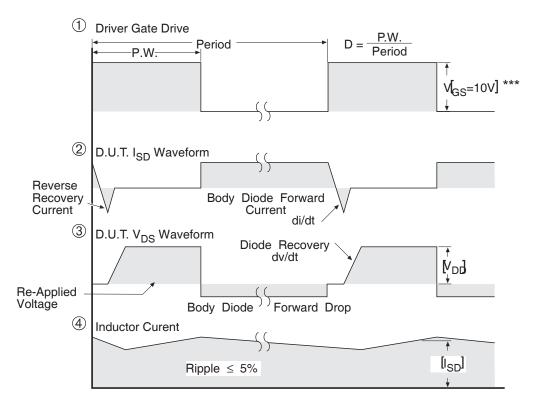


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



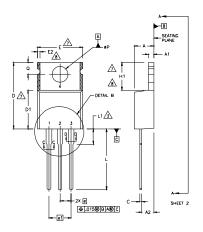
* Reverse Polarity of D.U.T for P-Channel

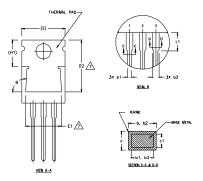


*** V_{GS} = 5.0V for Logic Level and 3V Drive Devices

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)





NOTES:

SYMBOL

Α

Α1

A2

b

ь1

b2

b3

С c1

D

D1

D2

Ε

E1

e e1 Н1

L

L1

øΡ

0

- DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994. DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].

- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- DIMENSION 61 & c1 APPLY TO BASE METAL ONLY.
 - CONTROLLING DIMENSION: INCHES. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E.H1,D2 & E1

DIMENSIONS

INCHES

MAX

.190

.055

.115

.040

.038 .070

.068

.024

.022

.650

.355

.507

.420

.350

.580

.250

.161

.135

MIN.

.140

020

.080

.015

-015

.045

.045

.014

.014

.560

.330

.480

.380

.330

-230

.500

,139

.100

NOTES

4,7

7,8

- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING
- AND SINGULATION IRREGULARITIES ARE ALLOWED.

MILLIMETERS

MAX

4.82

1.40

2.92

1.01

0.96

1,77

1.73

0.61

0.56

16.51

9.02

12,88

10.66

8.89

14,73

6.35

4.08

3,42

MIN.

3.56

0.51

2.04

0.38

0.38

1,15

1.15

0.36

0.36

14.22

8.38

12.19

9.66

8.38

5.85

12.70

3,54

2.54

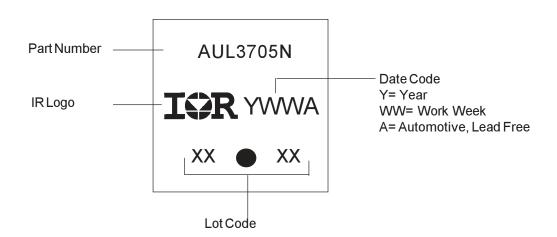
LEAD ASSIGNMENTS					
HEXFET					
1 GATE					

3,- SOURCE IGBTs, CoPACK

1.- GATE 2.- COLLECTOR 3.- EMITTER

DIDDES

TO-220AB Part Marking Information



Ordering Information

Base part	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRL3705N	TO-220	Tube	50	AUIRL3705N



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